

Switchmode Dual Ultrafast Power Rectifiers

Designed for use in switching power supplies. inverters and as free wheeling diodes. These state-of-the-art devices have the following:

Features

- *High Surge Capacity
- *Low Power Loss, High efficiency
- *150°C Operating Junction Temperature
- *Low Stored Charge Majority Carrier Conduction
- *Low Forward Voltage, High Current Capability
- *High-Switching Speed Recovery Time
- * Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O
- * In compliance with EU RoHs directives



MAXIMUM RATINGS

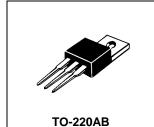
Characteristic	Symbol	UE10C20C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{R} \end{array}$	200	>
RMS Reverse Voltage	$V_{R(RMS)}$	140	V
Average Rectifier Forward Current (per diode) Total Device (Rated V_R)	I _{F(AV)}	5 10	Α
Peak Repetitive Forward Current (Rate V _R , Square Wave, 20kHz)	I _{FM}	10	Α
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware, single phase, 60Hz)	I _{FSM}	100	А
Operating and Storage Junction Temperature Range	T_J , T_{stg}	-65 to +150	$^{\circ}\!\mathbb{C}$

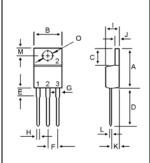
ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Maximum Instantaneous Forward Voltage ($I_F = 5 \text{ Amp } T_C = 25^{\circ}C$) ($I_F = 5 \text{ Amp } T_C = 125^{\circ}C$)	V _F		0.90 0.77	0.975	V
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_C = 25^{\circ}C$) (Rated DC Voltage, $T_C = 125^{\circ}C$)	I _R		0.01 2	5 	uA
Reverse Recovery Time ($I_F = 0.5 \text{ A}$, $I_R = 1.0$, $I_{rr} = 0.25 \text{ A}$)	T _{rr}		16	35	ns
Typical Thermal Resistance junction to case	$R_{\theta \ jc}$		3.0		°C/w
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	C _P		38		₽F

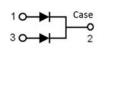
Ultrafast Power RECTIFIERS

10 AMPERES **200 VOLTS**

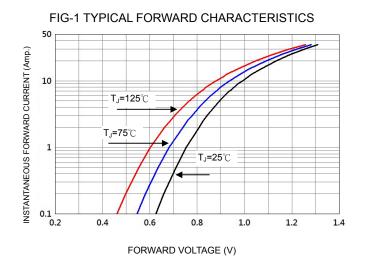


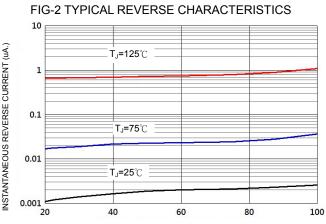


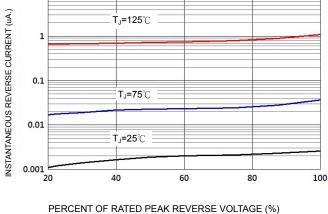
DIM	MILLIMETERS		
	MIN	MAX	
Α	14.68	16.00	
В	9.78	10.42	
С	5.02	6.60	
D	13.00	14.62	
E	3.10	4.19	
F	2.41	2.67	
G	1.10	1.67	
Н	0.69	1.01	
- 1	4.22	4.98	
J	1.14	1.40	
K	2.20	3.30	
L	0.28	0.61	
M	2.48	3.00	
0	3.50	4.00	

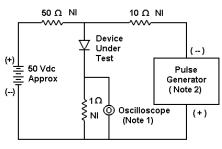




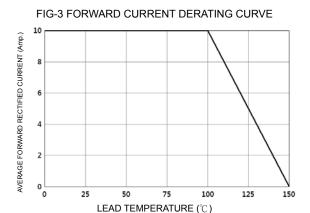


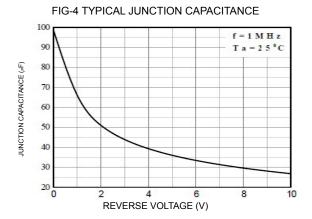


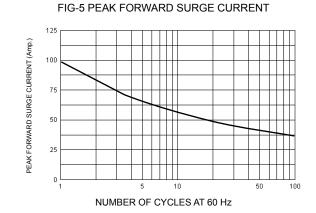


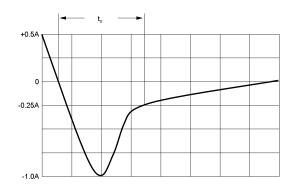


Notes: 1. Rise Time = 7 ns max. Input Impedance =1 M Ω , 22 pF 2. Rise Time = 10 ns max. Input Impedance = 50 Ω









Set time base for 10/20 ns/cm

FIG-6 Reverse Recovery Time Characteristic and Test Circuit Diagram



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